

WNMD2166

Dual N-Channel, 20V, 4.0A, Power MOSFET

[Http://www.willsemi.com](http://www.willsemi.com)

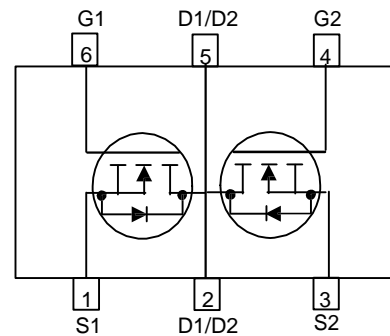
V _{DS} (V)	R _{ds(on)} ()	I _D (A)
20	0.022 @ V _{GS} =4.5V	4.0
	0.024 @ V _{GS} =3.1V	2.5
	0.027 @ V _{GS} =2.5V	2.0



Package

Descriptions

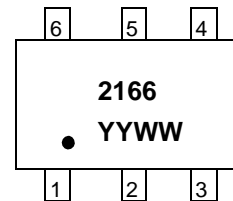
The WNMD2166 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS (ON)} with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product WNMD2166 is Pb-free.



Pin configuration (Top view)

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current
- Extremely Low Threshold Voltage
- Small package SOT-23-6L



2166 = Device Code
 YY = Year
 WW = Week

Marking

Applications

- Driver for Relay, Solenoid, Motor, LED etc.
- DC-DC converter circuit
- Power Switch
- Load Switch
- Charging

Order information

Device	Package	Shipping
WNMD2166	SOT-23-6L	3000/Reel&Tape

Absolute Maximum ratings

Parameter		Symbol	10 S	Steady State	Unit
Drain-Source Voltage		V_{DS}	+20		V
Gate-Source Voltage		V_{GS}	± 10		
Continuous Drain Current ^a	$T_A=25^\circ\text{C}$	I_D	5.0	4.0	A
	$T_A=70^\circ\text{C}$		3.8	3.5	
Maximum Power Dissipation ^a	$T_A=25^\circ\text{C}$	P_D	1.1	0.9	W
	$T_A=70^\circ\text{C}$		0.7	0.6	
Continuous Drain Current ^b	$T_A=25^\circ\text{C}$	I_D	4.0	3.5	A
	$T_A=70^\circ\text{C}$		3.5	3.0	
Maximum Power Dissipation ^b	$T_A=25^\circ\text{C}$	P_D	0.9	0.7	W
	$T_A=70^\circ\text{C}$		0.55	0.45	
Pulsed Drain Current ^c		I_{DM}	25		A
Operating Junction Temperature		T_J	-55~+150		$^\circ\text{C}$
Lead Temperature		T_L	260		$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55~+150		$^\circ\text{C}$

Thermal resistance ratings

Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ^a	t 10 s	R_{JA}	90	112	$^\circ\text{C/W}$
	Steady State		115	132	
Junction-to-Ambient Thermal Resistance ^b	t 10 s	R_{JA}	105	135	
	Steady State		138	162	
Junction-to-Case Thermal Resistance		R_{JC}	63	78	

a Surface mounted on FR-4 Board using 1 square inch pad size, 1oz copper

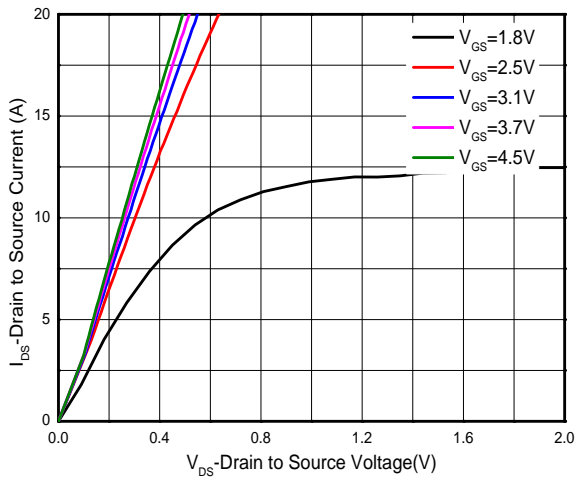
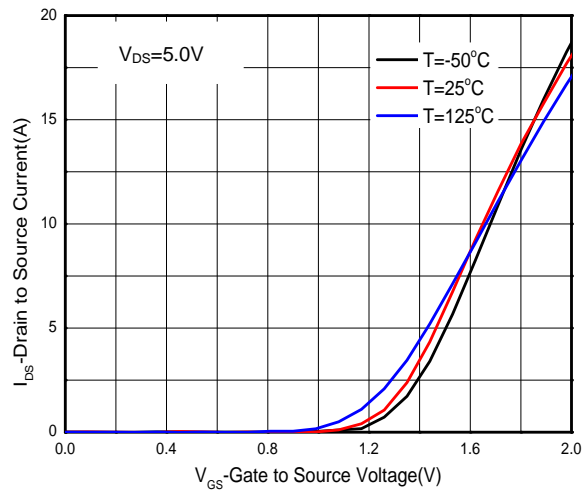
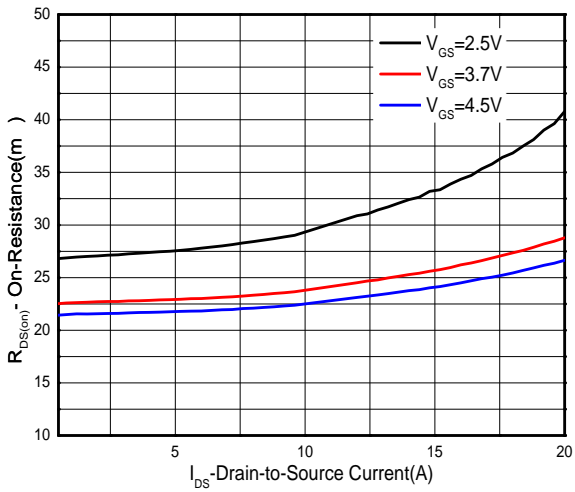
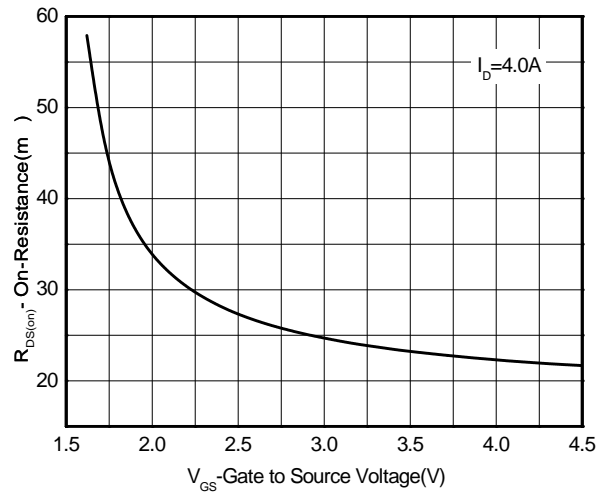
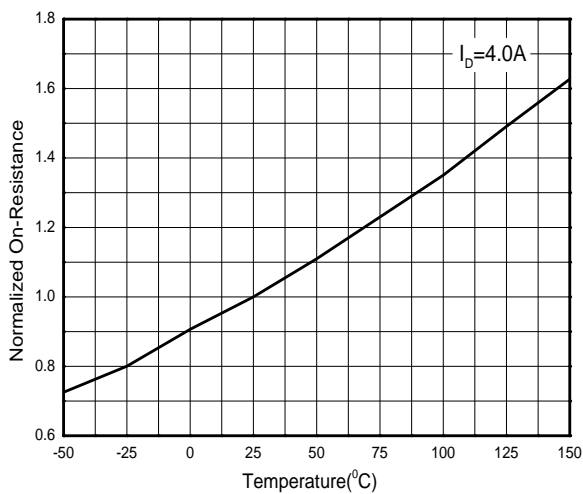
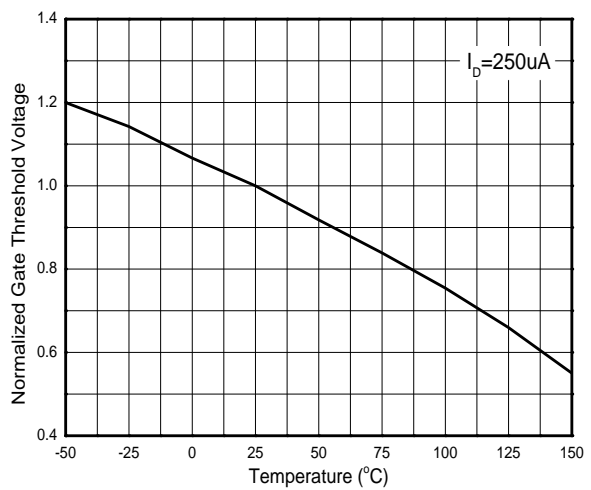
b Surface mounted on FR-4 board using minimum pad size, 1oz copper

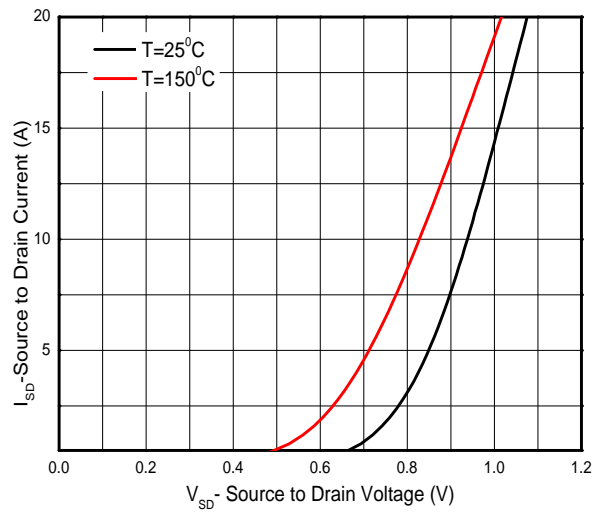
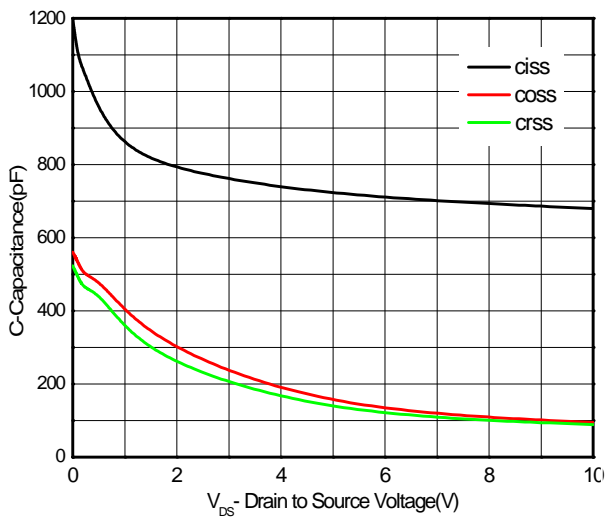
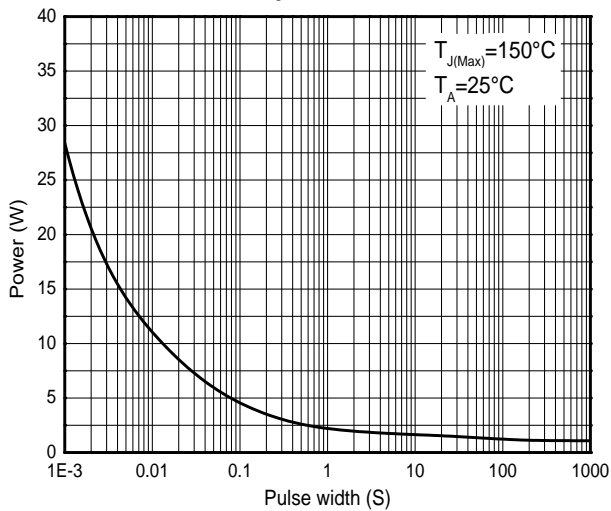
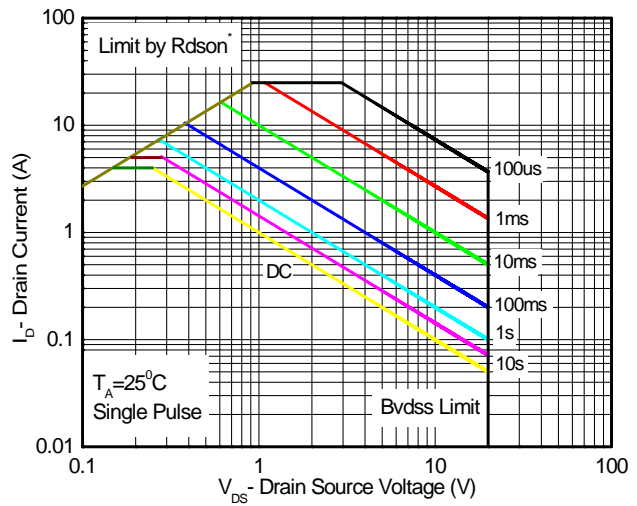
c Pulse width<380 μs , Duty Cycle<2%

d Maximum junction temperature $T_J=150^\circ\text{C}$.

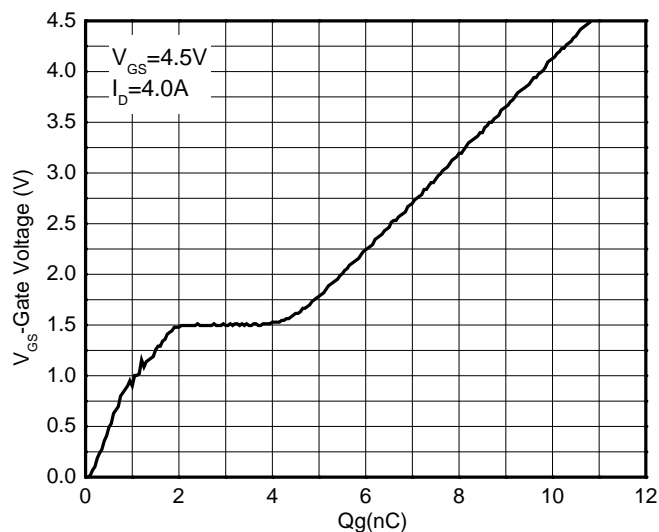
Electronics Characteristics (Ta=25°C, unless otherwise noted)

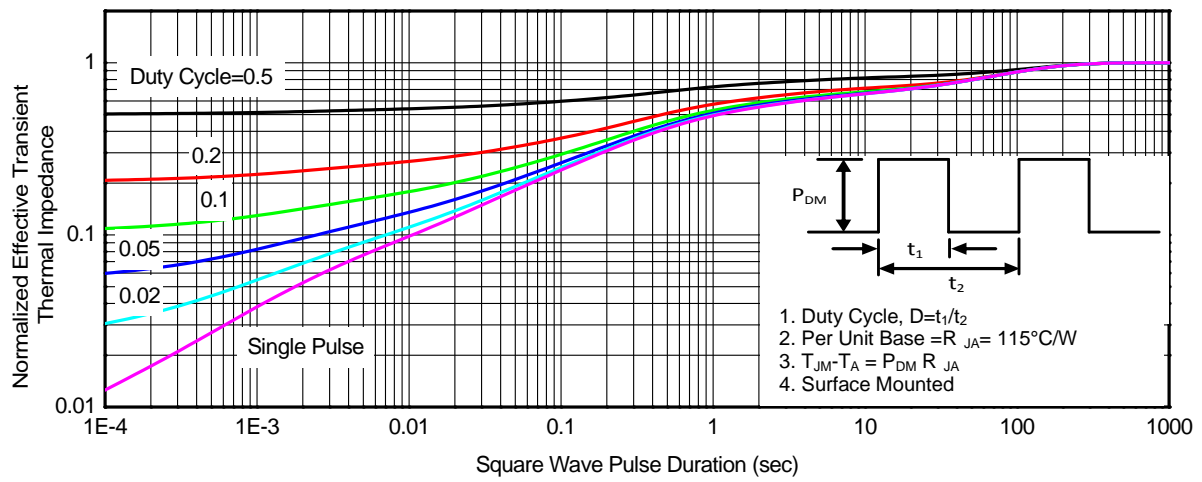
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\mu\text{A}$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$			1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	0.45	0.75	1.0	V
Drain-to-source On-resistance ^{b, c}	$R_{DS(on)}$	$V_{GS} = 4.5\text{V}, I_D = 4.0\text{A}$	15	22	27	m
		$V_{GS} = 3.7\text{V}, I_D = 4.0\text{A}$	17	23	30	
		$V_{GS} = 3.1\text{V}, I_D = 2.5\text{A}$	18	24	35	
		$V_{GS} = 2.5\text{V}, I_D = 2.0\text{A}$	20	27	37	
Forward Trans conductance	g_{fs}	$V_{DS} = 5.0\text{V}, I_D = 4.0\text{ A}$		11		S
CAPACITANCES, CHARGES						
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz},$ $V_{DS} = 10\text{ V}$		680		pF
Output Capacitance	C_{OSS}			95		
Reverse Transfer Capacitance	C_{RSS}			89		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V},$ $V_{DS} = 10\text{ V},$ $I_D = 4.0\text{A}$		10.8		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.8		
Gate-to-Source Charge	Q_{GS}			2.3		
Gate-to-Drain Charge	Q_{GD}			2.5		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_d(ON)$	$V_{GS} = 4.5\text{ V},$ $V_{DS} = 10\text{ V},$ $I_D = 4.0\text{ A},$ $R_G=6$		22		ns
Rise Time	t_r			32		
Turn-Off Delay Time	$t_d(OFF)$			60		
Fall Time	t_f			23		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 1.0\text{A}$		0.78	1.50	V

Typical Characteristics (Ta=25°C, unless otherwise noted)

Output characteristics

Transfer characteristics

On-Resistance vs. Drain current

On-Resistance vs. Gate-to-Source voltage

On-Resistance vs. Junction temperature

Threshold voltage vs. Temperature

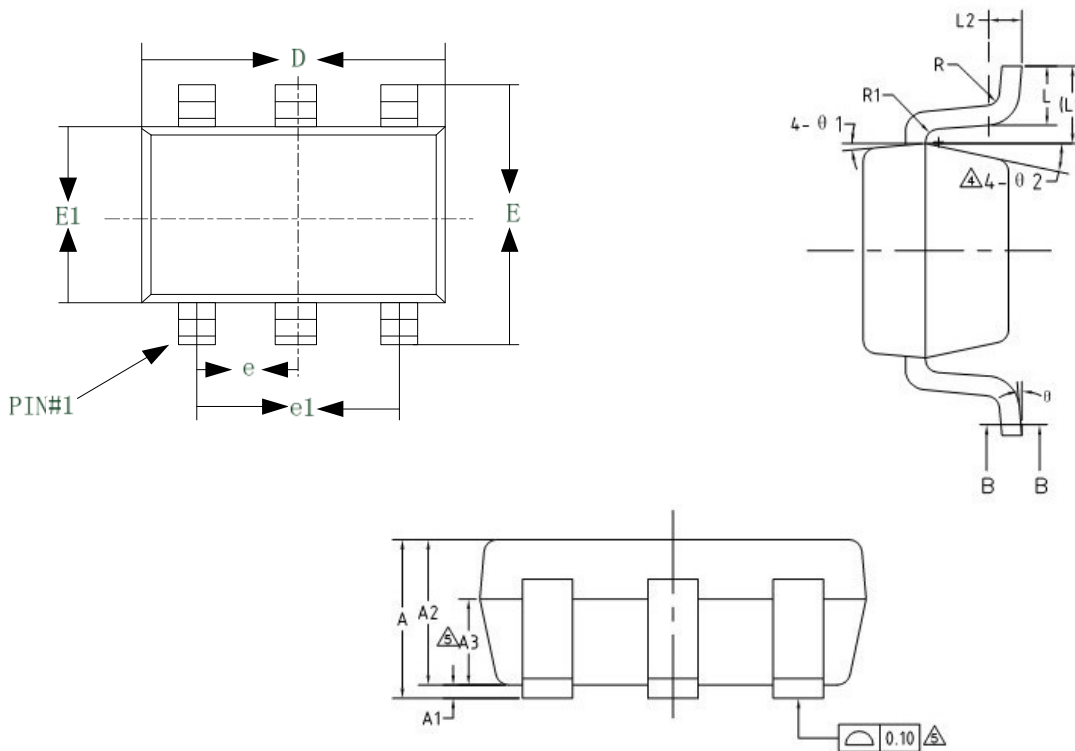

Capacitance

Single pulse power
Body diode forward voltage


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe operating power

Gate charge Characteristics



Transient thermal response (Junction-to-Ambient)

Package outline dimensions
SOT-23-6L


Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	-	-	1.25
A1	0	-	0.15
A2	1.00	1.10	1.20
A3	0.60	0.65	0.70
b	0.36	-	0.50
b1	0.36	0.38	0.45
c	0.14	-	0.20
c1	0.14	0.15	0.16
D	2.826	2.926	3.026
E	2.60	2.80	3.00
E1	1.526	1.626	1.726
e	0.90	0.95	1.00
e1	1.80	1.90	2.00
L	0.35	0.45	0.60
L1	0.59REF		
L2	0.25BSC		
R	0.10	-	-
R1	0.10	-	0.20
θ	0°		8°
θ1	3°	5°	7°
θ2	6°		14°